

MULTIPLE (QUAD) PNP SILICON SWITCHING TRANSISTOR Qualified per MIL-PRF-19500/558

Devices Qualified Level

2N6987 2N6987U

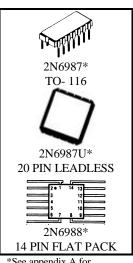
2N6988

JAN
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MAXIMUM RATINGS (1)

Ratings	Symbol	Value	Units
Collector-Emitter Voltage (4)	V_{CEO}	60	Vdc
Collector-Base Voltage (4)	V_{CBO}	60	Vdc
Emitter-Base Voltage (4)	V_{EBO}	5.0	Vdc
Collector Current	I_{C}	600	mAdc
Total Power Dissipation @ $T_A = +25^{\circ}C$ $2N6987^{(2)}$ $2N6987U^{(2)}$ $2N6988^{(3)}$	P_{T}	1.5 1.0 0.4	W
Operating & Storage Junction Temperature Range	Top, Tstg	-65 to +200	°C

- 1) Maximum voltage between transistors shall be ≥ 500 Vdc
- 2) Derate linearly 8.57 mW/ $^{\circ}$ C above $T_A = +25^{\circ}$ C
- 3) Derate linearly 2.286 mW/ $^{\circ}$ C above $T_A = +25^{\circ}$ C.
- 4) Ratings apply to each transistor in the array.



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS (T_A = 25⁰C unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage	V	60		Vdc
$I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	00		vac
Collector-Base Cutoff Current				
$V_{CB} = 60 \text{ Vdc}$	I_{CBO}		10	μAdc
$V_{CB} = 50 \text{ Vdc}$	<u> </u>		10	ηAdc
Emitter-Base Cutoff Current				
$V_{BE} = 5.0 \text{ Vdc}$	$I_{ m EBO}$		10	μAdc
$V_{EB} = 3.5 \text{ Vdc}$			50	ηAdc

2N6987, 2N6988 JAN, SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS				
Forward-Current Transfer Ratio				
$I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$		75		
$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$		100	450	
$I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	$h_{ m FE}$	100	200	
$I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$		100	300	
$I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$		50		
Collector-Emitter Saturation Voltage				
$I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$	V _{CE(sat)}		0.4	
$I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$			1.6	Vdc
Base-Emitter Voltage				
$I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$	V _{BE(sat)}		1.3	Vdc
$I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$			2.6	
DYNAMIC CHARACTERISTICS				
Magnitude of Small-Signal Short-Circuit				
Forward-Current Transfer Ratio	$ h_{\rm fe} $	2.0	8.0	
$I_C = 50 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$				
Small-Signal Short-Circuit Forward Current Transfer Ratio	h	100		
$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$	h _{fe}			
Output Capacitance	C		8.0	pF
$V_{CB} = 10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C_{obo}		6.0	pr
Input Capacitance	C_{ibo}		30	рF
$V_{EB} = 2.0 \text{ Vdc}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	Cibo		50	pF

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